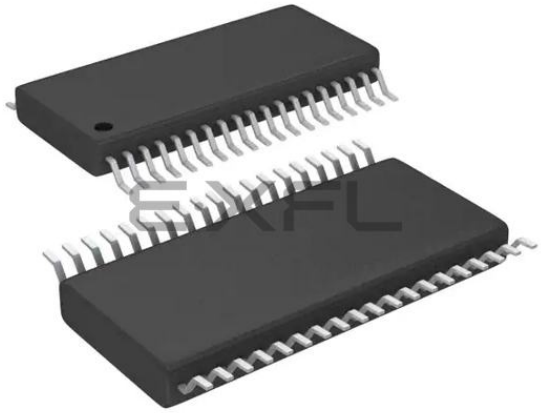
Infineon Technologies - XMC1100T038F0064ABXUMA1 Datasheet



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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M0
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	I²C, LINbus, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, I²S, POR, PWM, WDT
Number of I/O	26
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 5.5V
Data Converters	A/D 12x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	38-TFSOP (0.173", 4.40mm Width)
Supplier Device Package	PG-TSSOP-38-9
Purchase URL	https://www.e-xfl.com/product-detail/infineon-technologies/xmc1100t038f0064abxuma1

XMC1100 Data Sheet

Revision History: V1.7 2016-08

Previous Version: V1.6	
Page	Subjects
many	Added XMC™ trademark
Page 23	Removed ADC channels from Port I/O Functions table, which are not available in XMC1100 (G1CH0, G1CH2, G1CH3, G1CH4).
Page 36	Removed auxiliary V_{REFGND} for G1CH0, as this channel is not available in XMC1100.
Page 36	Adjusted ADC sample time and sample rate to configurable limits.
Page 46	Flash Memory Parameters Table: • Erase time per page parameter is renamed to Erase time per page / sector. • Erase cycles parameter is renamed to include test condition of sum of page and sector erase cycles. • Added parameter for fixed wait states configuration.

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About this Document

This Data Sheet is addressed to embedded hardware and software developers. It provides the reader with detailed descriptions about the ordering designations, available features, electrical and physical characteristics of the XMC1100 series devices.

The document describes the characteristics of a superset of the XMC1100 series devices. For simplicity, the various device types are referred to by the collective term XMC1100 throughout this document.

XMC™1000 Family User Documentation

The set of user documentation includes:

- **Reference Manual**
  – decribes the functionality of the superset of devices.
- **Data Sheets**
  – list the complete ordering designations, available features and electrical characteristics of derivative devices.
- **Errata Sheets**
  – list deviations from the specifications given in the related Reference Manual or Data Sheets. Errata Sheets are provided for the superset of devices.

Attention: Please consult all parts of the documentation set to attain consolidated knowledge about your device.

Application related guidance is provided by **Users Guides** and **Application Notes**.

Please refer to **http://www.infineon.com/xmc1000** to get access to the latest versions of those documents.

Table 1 Synopsis of XMC1100 Device Types (cont'd)

Derivative	Package	Flash Kbytes	SRAM Kbytes
XMC1100-Q040F0032	PG-VQFN-40-13	32	16
XMC1100-Q040F0064	PG-VQFN-40-13	64	16

1.3 Device Type Features

The following table lists the available features per device type.

Table 2 Features of XMC1100 Device Types[1)]

Derivative	ADC channel
XMC1100-T016	6
XMC1100-T038	12
XMC1100-Q024	8
XMC1100-Q040	12

1) Features that are not included in this table are available in all the derivatives

Table 3 ADC Channels

Package	VADC0 G0	VADC0 G1
PG-TSSOP-16	CH0..CH5	-
PG-TSSOP-38	CH0..CH7	CH1, CH5 .. CH7
PG-VQFN-24	CH0..CH7	-
PG-VQFN-40	CH0..CH7	CH1, CH5 .. CH7

1.4 Chip Identification Number

The Chip Identification Number allows software to identify the marking. It is a 8 words value with the most significant 7 words stored in Flash configuration sector 0 (CS0) at address location : 1000 $0F00_H$ (MSB) - 1000 $0F1B_H$ (LSB). The least significant word and most significant word of the Chip Identification Number are the value of registers DBGROMID and IDCHIP, respectively.

2.2 Pin Configuration and Definition

The following figures summarize all pins, showing their locations on the different packages.

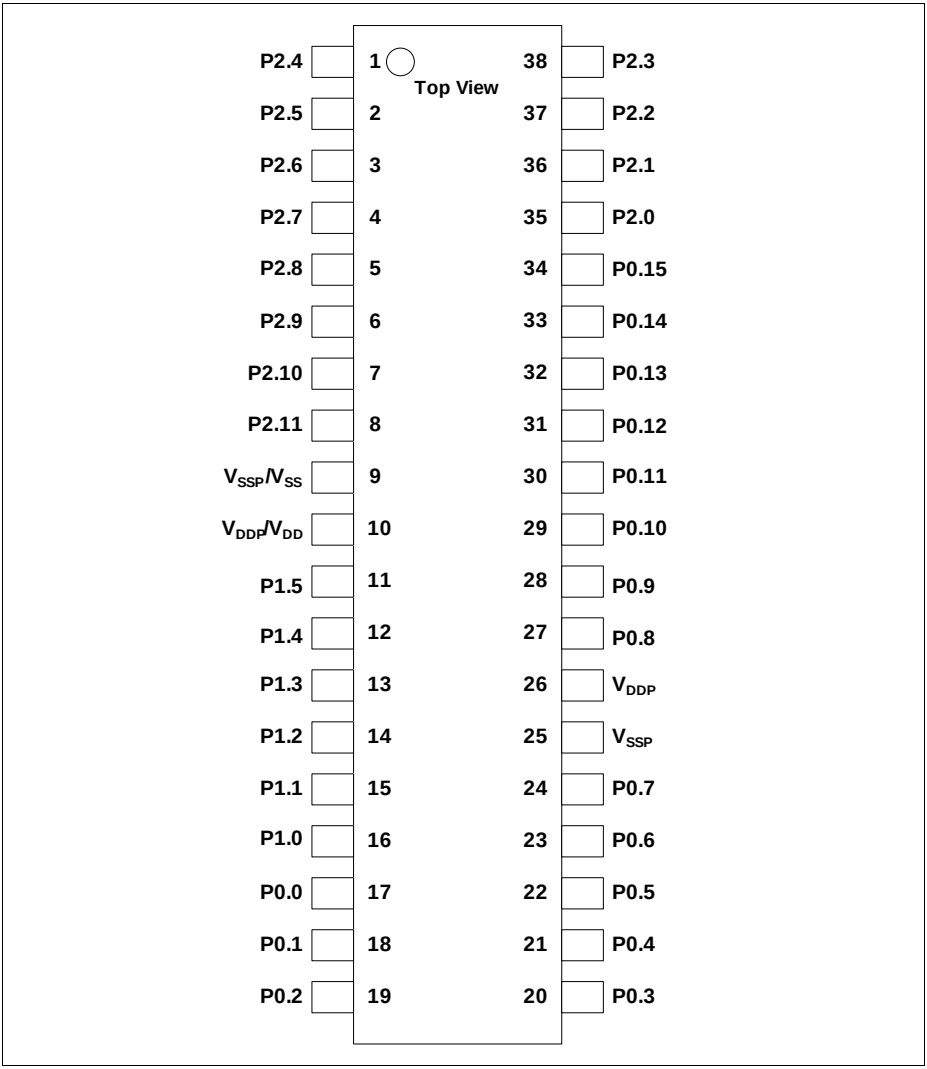


Figure 4 XMC1100 PG-TSSOP-38 Pin Configuration (top view)

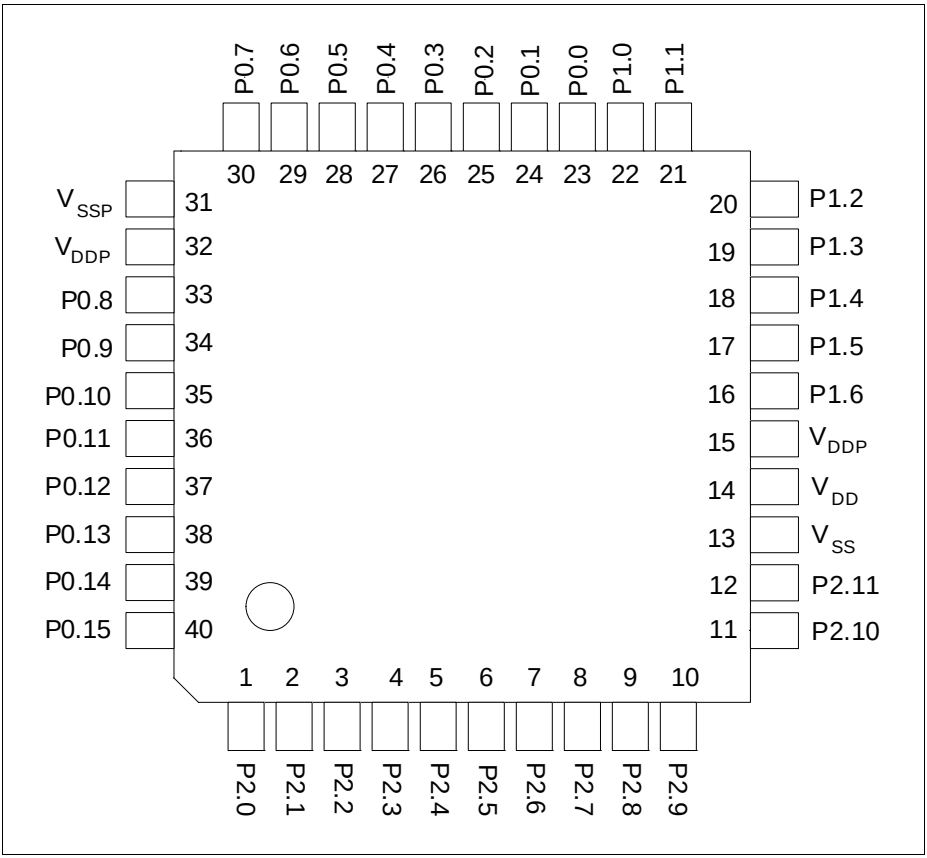


Figure 7 XMC1100 PG-VQFN-40 Pin Configuration (top view)

2.2.1 Package Pin Summary

The following general building block is used to describe each pin:

Table 5 Package Pin Mapping Description

Function	Package A	Package B	...	Pad Type
Px.y	N	N		Pad Class

The table is sorted by the “Function” column, starting with the regular Port pins (Px.y), followed by the supply pins.

The following columns, titled with the supported package variants, lists the package pin number to which the respective function is mapped in that package.

The “Pad Type” indicates the employed pad type:

- STD_INOUT (standard bi-directional pads)
- STD_INOUT/AN (standard bi-directional pads with analog input)
- High Current (high current bi-directional pads)
- STD_IN/AN (standard input pads with analog input)
- Power (power supply)

Details about the pad properties are defined in the Electrical Parameters.

Table 6 Package Pin Mapping

Function	VQFN 40	TSSOP 38	VQFN 24	TSSOP 16	Pad Type	Notes
P0.0	23	17	15	7	STD_INOUT	
P0.1	24	18	-	-	STD_INOUT	
P0.2	25	19	-	-	STD_INOUT	
P0.3	26	20	-	-	STD_INOUT	
P0.4	27	21	-	-	STD_INOUT	
P0.5	28	22	16	8	STD_INOUT	
P0.6	29	23	17	9	STD_INOUT	
P0.7	30	24	18	10	STD_INOUT	
P0.8	33	27	19	11	STD_INOUT	
P0.9	34	28	20	12	STD_INOUT	
P0.10	35	29	-	-	STD_INOUT	
P0.11	36	30	-	-	STD_INOUT	
P0.12	37	31	21	-	STD_INOUT	

Table 6 Package Pin Mapping (cont'd)

Function	VQFN 40	TSSOP 38	VQFN 24	TSSOP 16	Pad Type	Notes
P0.13	38	32	22	-	STD_INOUT	
P0.14	39	33	23	13	STD_INOUT	
P0.15	40	34	24	14	STD_INOUT	
P1.0	22	16	14	-	High Current	
P1.1	21	15	13	-	High Current	
P1.2	20	14	12	-	High Current	
P1.3	19	13	11	-	High Current	
P1.4	18	12	-	-	High Current	
P1.5	17	11	-	-	High Current	
P1.6	16	-	-	-	STD_INOUT	
P2.0	1	35	1	15	STD_INOUT/ AN	
P2.1	2	36	2	-	STD_INOUT/ AN	
P2.2	3	37	3	-	STD_IN/AN	
P2.3	4	38	-	-	STD_IN/AN	
P2.4	5	1	-	-	STD_IN/AN	
P2.5	6	2	-	-	STD_IN/AN	
P2.6	7	3	4	16	STD_IN/AN	
P2.7	8	4	5	1	STD_IN/AN	
P2.8	9	5	5	1	STD_IN/AN	
P2.9	10	6	6	2	STD_IN/AN	
P2.10	11	7	7	3	STD_INOUT/ AN	
P2.11	12	8	8	4	STD_INOUT/ AN	
VSS	13	9	9	5	Power	Supply GND, ADC reference GND
VDD	14	10	10	6	Power	Supply VDD, ADC reference voltage/ ORC reference voltage

Table 6 Package Pin Mapping (cont'd)

Function	VQFN 40	TSSOP 38	VQFN 24	TSSOP 16	Pad Type	Notes
VDDP	15	10	10	6	Power	When VDD is supplied, VDDP has to be supplied with the same voltage.
VSSP	31	25	-	-	Power	I/O port ground
VDDP	32	26	-	-	Power	I/O port supply
VSSP	Exp. Pad	-	Exp. Pad	-	Power	**Exposed Die Pad** The exposed die pad is connected internally to VSSP. For proper operation, it is mandatory to connect the exposed pad to the board ground. For thermal aspects, please refer to the Package and Reliability chapter.

2.2.2 Port I/O Function Description

The following general building block is used to describe the I/O functions of each PORT pin:

Table 7 Port I/O Function Description

Function	Outputs		Inputs	
	ALT1	ALTn	Input	Input
P0.0		MODA.OUT	MODC.INA	
Pn.y	MODA.OUT		MODA.INA	MODC.INB

Table 10 Hardware Controlled I/O Functions

Function	Outputs		Inputs		Pull Control			
	HWO0	HWO1	HWI0	HWI1	HW0_PD	HW0_PU	HW1_PD	HW1_PU
P0.0								
P0.1								
P0.2								
P0.3								
P0.4								
P0.5								
P0.6								
P0.7								
P0.8								
P0.9								
P0.10								
P0.11								
P0.12								
P0.13								
P0.14								
P0.15								
P1.0		USIC0_CH0. DOUT0		USIC0_CH0. HWIN0				
P1.1		USIC0_CH0. DOUT1		USIC0_CH0. HWIN1				
P1.2		USIC0_CH0. DOUT2		USIC0_CH0. HWIN2				
P1.3		USIC0_CH0. DOUT3		USIC0_CH0. HWIN3				
P1.4								
P1.5								
P1.6								
P2.0								
P2.1								
P2.2							$\overline{\text{CCU40.OUT3}}$	CCU40.OUT3
P2.3								
P2.4								

3 Electrical Parameter

This section provides the electrical parameter which are implementation-specific for the XMC1100.

3.1 General Parameters

3.1.1 Parameter Interpretation

The parameters listed in this section represent partly the characteristics of the XMC1100 and partly its requirements on the system. To aid interpreting the parameters easily when evaluating them for a design, they are indicated by the abbreviations in the “Symbol” column:

- **CC**
  Such parameters indicate **C**ontroller **C**haracteristics, which are distinctive feature of the XMC1100 and must be regarded for a system design.
- **SR**
  Such parameters indicate **S**ystem **R**equirements, which must be provided by the application system in which the XMC1100 is designed in.

Table 13 PN-Junction Characterisitics for positive Overload

Pad Type	I_{OV} = 5 mA, T_J = -40 °C	I_{OV} = 5 mA, T_J = 115 °C
Standard, High-current, AN/DIG_IN	$V_{IN} = V_{DDP}$ + 0.5 V	$V_{IN} = V_{DDP}$ + 0.5 V

Table 14 PN-Junction Characterisitics for negative Overload

Pad Type	I_{OV} = 5 mA, T_J = -40 °C	I_{OV} = 5 mA, T_J = 115 °C
Standard, High-current, AN/DIG_IN	$V_{IN} = V_{SS}$ - 0.5 V	$V_{IN} = V_{SS}$ - 0.5 V

Table 16 Input/Output Characteristics (Operating Conditions apply) (cont'd)

Parameter	Symbol		Limit Values		Unit	Test Conditions
			Min.	Max.		
Input low voltage on port pins (Large Hysteresis)	V_{ILPL}	SR	–	0.08 × V_{DDP}	V	CMOS Mode (5 V, 3.3 V & 2.2 V)[10]
Input high voltage on port pins (Large Hysteresis)	V_{IHPL}	SR	0.85 × V_{DDP}	–	V	CMOS Mode (5 V, 3.3 V & 2.2 V)[10]
Rise time on High Current Pad[1]	t_{HCPR}	CC	–	9	ns	50 pF @ 5 V[2]
			–	12	ns	50 pF @ 3.3 V[3]
			–	25	ns	50 pF @ 1.8 V[4]
Fall time on High Current Pad[1]	t_{HCPF}	CC	–	9	ns	50 pF @ 5 V[2]
			–	12	ns	50 pF @ 3.3 V[3]
			–	25	ns	50 pF @ 1.8 V[4]
Rise time on Standard Pad[1]	t_R	CC	–	12	ns	50 pF @ 5 V[5]
			–	15	ns	50 pF @ 3.3 V[6]
			–	31	ns	50 pF @ 1.8 V[7]
Fall time on Standard Pad[1]	t_F	CC	–	12	ns	50 pF @ 5 V[5]
			–	15	ns	50 pF @ 3.3 V[6]
			–	31	ns	50 pF @ 1.8 V[7]
Input Hysteresis[8]	HYS	CC	0.08 × V_{DDP}	–	V	CMOS Mode (5 V), Standard Hysteresis
			0.03 × V_{DDP}	–	V	CMOS Mode (3.3 V), Standard Hysteresis
			0.02 × V_{DDP}	–	V	CMOS Mode (2.2 V), Standard Hysteresis
			0.5 × V_{DDP}	0.75 × V_{DDP}	V	CMOS Mode(5 V), Large Hysteresis
			0.4 × V_{DDP}	0.75 × V_{DDP}	V	CMOS Mode(3.3 V), Large Hysteresis
			0.2 × V_{DDP}	0.65 × V_{DDP}	V	CMOS Mode(2.2 V), Large Hysteresis

8) Hysteresis is implemented to avoid meta stable states and switching due to internal ground bounce. It cannot be guaranteed that it suppresses switching due to external system noise.

9) An additional error current (I_{INJ}) will flow if an overload current flows through an adjacent pin.

10) However, for applications with strict low power-down current requirements, it is mandatory that no active voltage source is supplied at any GPIO pin when V_{DDP} is powered off.

Table 17 ADC Characteristics (Operating Conditions apply)[1] (cont'd)

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Maximum sample rate in 8-bit mode [3]	f_{C8} CC	–	–	f_{ADC} / 38.5	–	1 sample pending
		–	–	f_{ADC} / 54.5	–	2 samples pending
RMS noise [4]	EN_{RMS} CC	–	1.5	–	LSB 12	DC input, V_{DD} = 5.0 V, V_{AIN} = 2.5 V, 25°C
DNL error	EA_{DNL} CC	–	±2.0	–	LSB 12	
INL error	EA_{INL} CC	–	±4.0	–	LSB 12	
Gain error with external reference	EA_{GAIN} CC	–	±0.5	–	%	SHSCFG.AREF = 00_B (calibrated)
Gain error with internal reference [5]	EA_{GAIN} CC	–	±3.6	–	%	SHSCFG.AREF = $1X_B$ (calibrated), -40°C - 105°C
		–	±2.0	–	%	SHSCFG.AREF = $1X_B$ (calibrated), 0°C - 85°C
Offset error	EA_{OFF} CC	–	±8.0	–	mV	Calibrated, V_{DD} = 5.0 V

1) The parameters are defined for ADC clock frequency f_{SH} = 32MHz.

2) No pending samples assumed, excluding sampling time and calibration.

3) Includes synchronization and calibration (average of gain and offset calibration).

4) This parameter can also be defined as an SNR value: SNR[dB] = 20 × log(A_{MAXeff} / N_{RMS}).
With $A_{MAXeff} = 2^N / 2$, SNR[dB] = 20 × log (2048 / N_{RMS}) [N = 12].
N_{RMS} = 1.5 LSB12, therefore, equals SNR = 20 × log (2048 / 1.5) = 62.7 dB.

5) Includes error from the reference voltage.

3.2.3 Temperature Sensor Characteristics

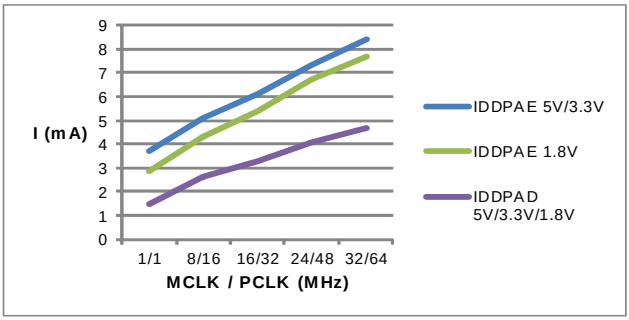
Note: These parameters are not subject to production test, but verified by design and/or characterization.

Table 18 Temperature Sensor Characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Measurement time	t_M CC	–	–	10	ms	
Temperature sensor range	T_{SR} SR	-40	–	115	°C	
Sensor Accuracy[1)]	T_{TSAL} CC	-6	–	6	°C	T_J > 20°C
		-10	–	10	°C	0°C ≤ T_J ≤ 20°C
		-18	–	18	°C	-25°C ≤ T_J < 0°C
		-31	–	31	°C	-40°C ≤ T_J < -25°C
Start-up time after enabling	t_{TSSTE} SR	–	–	15	µs	

1) The temperature sensor accuracy is independent of the supply voltage.

Figure 11 shows typical graphs for active mode supply current for V_{DDP} = 5V, V_{DDP} = 3.3V, V_{DDP} = 1.8V across different clock frequencies.



Condition:
1. TA = +25° C

Figure 11 Active mode, a) peripherals clocks enabled, b) peripherals clocks disabled: Supply current I_{DDPA} over supply voltage V_{DDP} for different clock frequencies

3.3.4 Serial Wire Debug Port (SW-DP) Timing

The following parameters are applicable for communication through the SW-DP interface.

Note: These parameters are not subject to production test, but verified by design and/or characterization.

Table 25 SWD Interface Timing Parameters(Operating Conditions apply)

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
SWDCLK high time	t_1 SR	50	–	500000	ns	–
SWDCLK low time	t_2 SR	50	–	500000	ns	–
SWDIO input setup to SWDCLK rising edge	t_3 SR	10	–	–	ns	–
SWDIO input hold after SWDCLK rising edge	t_4 SR	10	–	–	ns	–
SWDIO output valid time after SWDCLK rising edge	t_5 CC	–	–	68	ns	C_L = 50 pF
		–	–	62	ns	C_L = 30 pF
SWDIO output hold time from SWDCLK rising edge	t_6 CC	4	–	–	ns	

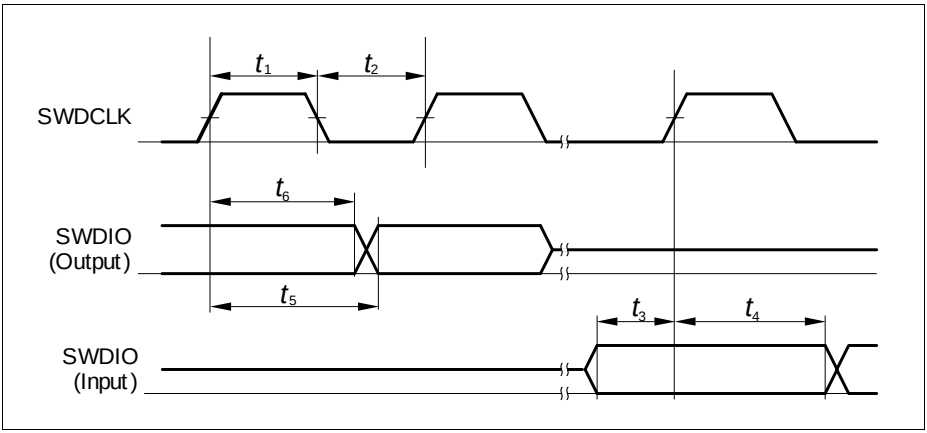


Figure 18 SWD Timing

Table 30 USIC IIC Fast Mode Timing[1)]

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Fall time of both SDA and SCL	t_1 CC/SR	20 + 0.1*C_b [2)]	-	300	ns	
Rise time of both SDA and SCL	t_2 CC/SR	20 + 0.1*C_b	-	300	ns	
Data hold time	t_3 CC/SR	0	-	-	µs	
Data set-up time	t_4 CC/SR	100	-	-	ns	
LOW period of SCL clock	t_5 CC/SR	1.3	-	-	µs	
HIGH period of SCL clock	t_6 CC/SR	0.6	-	-	µs	
Hold time for (repeated) START condition	t_7 CC/SR	0.6	-	-	µs	
Set-up time for repeated START condition	t_8 CC/SR	0.6	-	-	µs	
Set-up time for STOP condition	t_9 CC/SR	0.6	-	-	µs	
Bus free time between a STOP and START condition	t_{10} CC/SR	1.3	-	-	µs	
Capacitive load for each bus line	C_b SR	-	-	400	pF	

1) Due to the wired-AND configuration of an IIC bus system, the port drivers of the SCL and SDA signal lines need to operate in open-drain mode. The high level on these lines must be held by an external pull-up device, approximalely 10 kOhm for operation at 100 kbit/s, approximately 2 kOhm for operation at 400 kbit/s.

2) C_b refers to the total capacitance of one bus line in pF.

4.2 Package Outlines

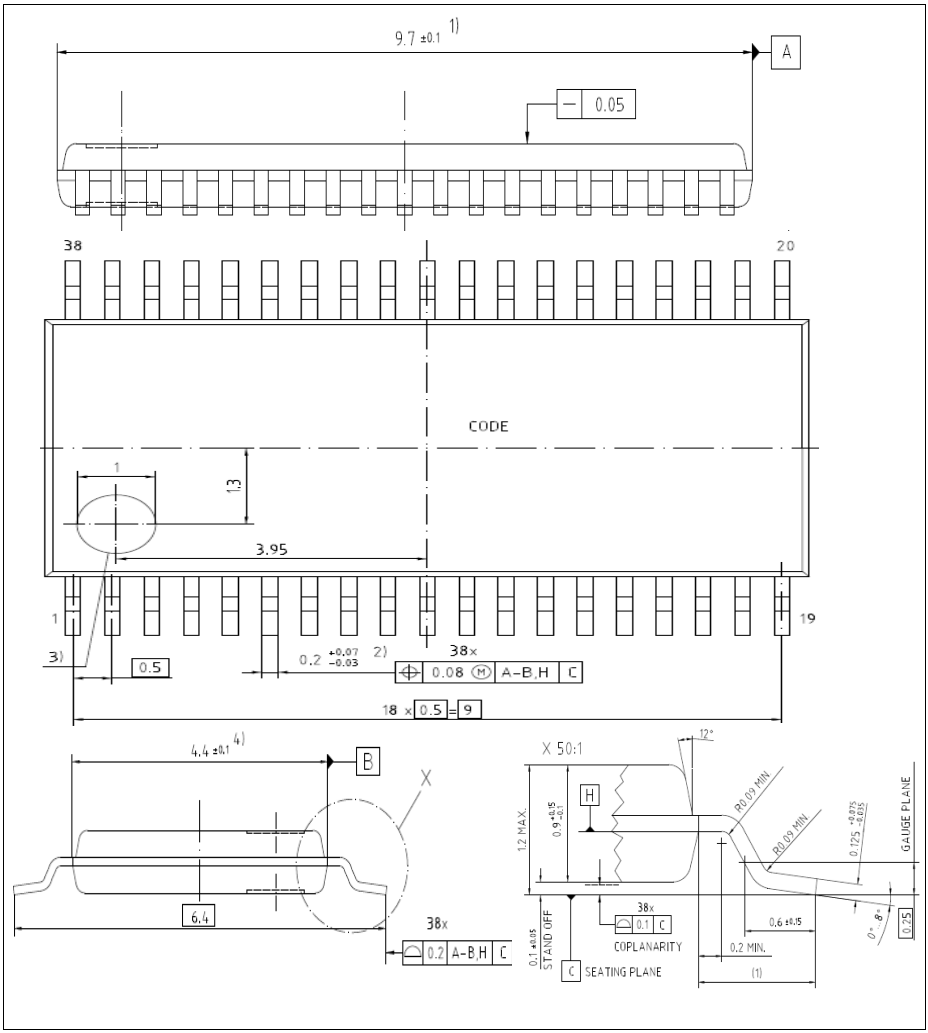


Figure 23 PG-TSSOP-38-9

5 Quality Declaration

Table 34 shows the characteristics of the quality parameters in the XMC1100.

Table 34 Quality Parameters

Parameter	Symbol	Limit Values		Unit	Notes
		Min.	Max.		
ESD susceptibility according to Human Body Model (HBM)	V_{HBM} SR	-	2000	V	Conforming to EIA/JESD22-A114-B
ESD susceptibility according to Charged Device Model (CDM) pins	V_{CDM} SR	-	500	V	Conforming to JESD22-C101-C
Moisture sensitivity level	MSL CC	-	3	-	JEDEC J-STD-020D
Soldering temperature	T_{SDR} SR	-	260	°C	Profile according to JEDEC J-STD-020D